



# THE DATASHEET OF SL2308A



## 60V/3A N-Channel MOSFET

### Features

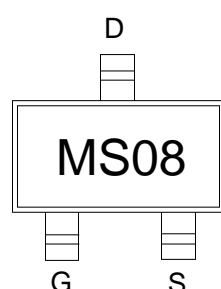
- Excellent package for good heat dissipation
- Ultra low gate charge
- Low reverse transfer capacitance
- Fast switching capability
- Avalanche energy specified

### Product Summary

$V_{DS}$	$R_{DS(ON)}$ MAX	$I_D$ MAX
60V	100mΩ@10V	3A
	150mΩ@4.5V	

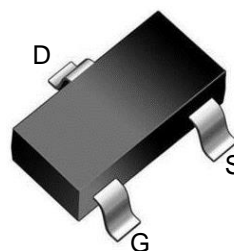
### Application

- Power switching application

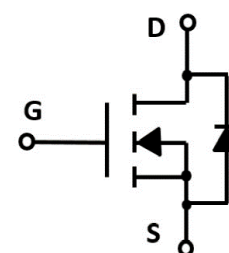


MS08: Device code

Marking and pin assignment



SOT-23 top view



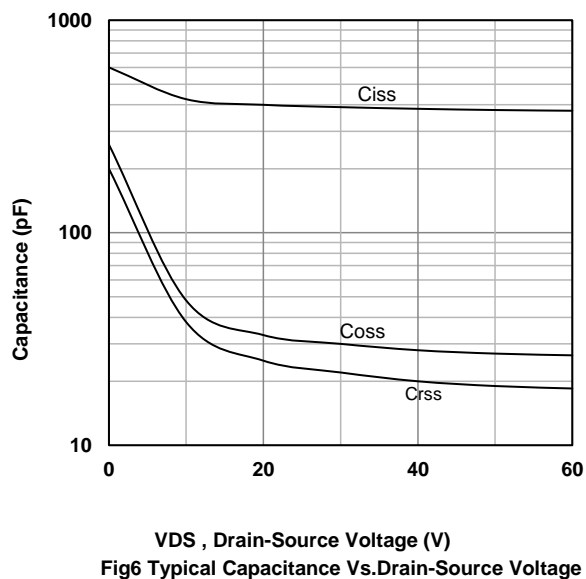
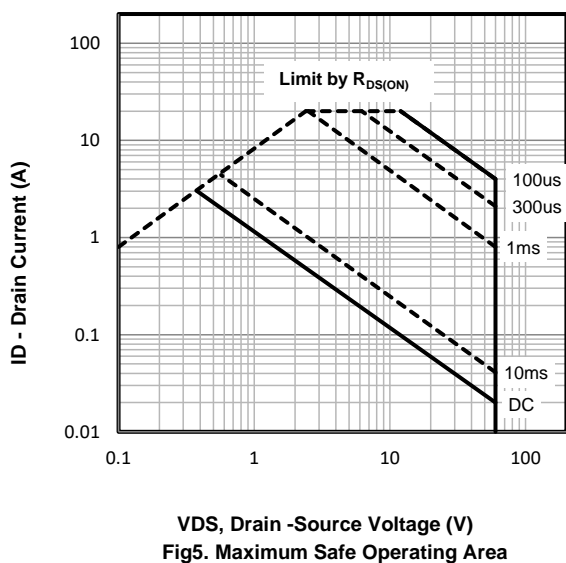
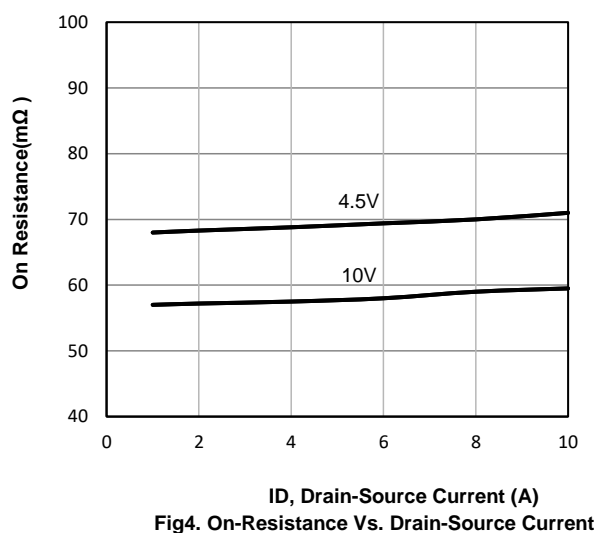
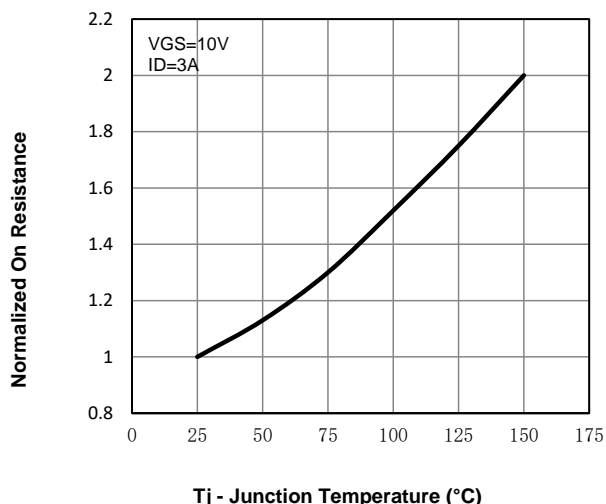
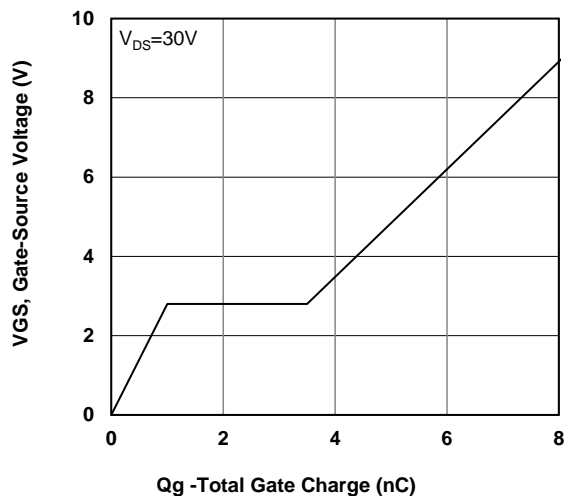
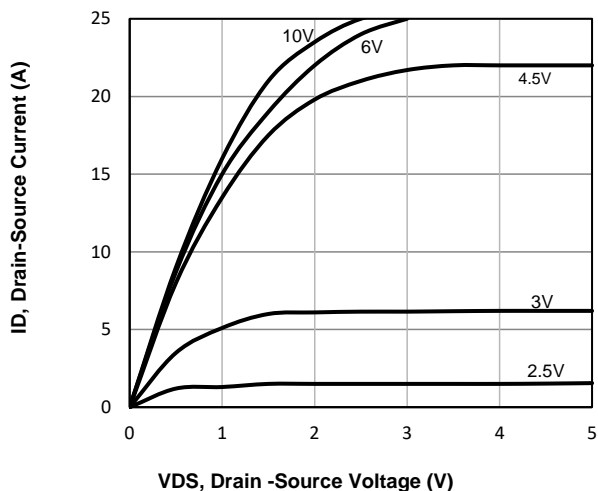
Schematic diagram

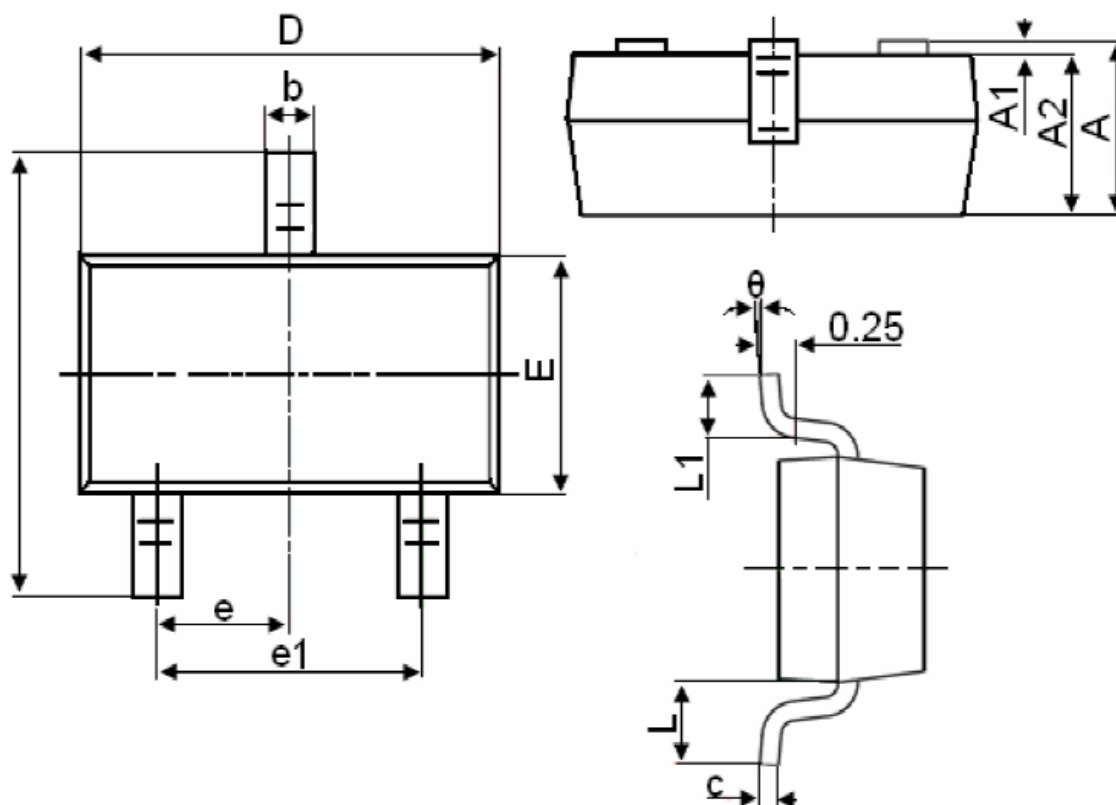


Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
<b>Common Ratings (TC=25°C Unless Otherwise Noted)</b>				
$V_{DS}$	Drain-Source Breakdown Voltage		60	V
$V_{GS}$	Gate-Source Voltage		±20	V
$T_J$	Maximum Junction Temperature		150	°C
$T_{STG}$	Storage Temperature Range		-55 to 150	°C
$I_S$	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$	3	A
<b>Mounted on Large Heat Sink</b>				
$I_{DM}$	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$	12	A
$I_D$	Continuous Drain Current@GS=10V	$T_C=25^\circ\text{C}$	3	A
$P_D$	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	0.35	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient>(*1 in2 Pad of 2-oz Copper), Max.)		375	°C/W

<b>Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)</b>						
<b>Symbol</b>	<b>Parameter</b>	<b>Condition</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>
<b>Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
BV <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	60	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	VDS=60V, VGS=0V	--	--	1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.1	1.7	2.5	V
R <sub>DS(on)</sub>	Drain-Source On-State Resistance	VGS=10V, ID=3A	--	58	100	mΩ
		VGS=4.5V, ID=2A	--	70	150	
<b>Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
C <sub>ISS</sub>	Input Capacitance	VDS=30V, VGS=0V, f=1MHz	--	400	--	pF
C <sub>OSS</sub>	Output Capacitance		--	28	--	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		--	23	--	pF
<b>Switching Characteristics</b>						
Q <sub>g</sub>	Total Gate Charge	VDS=30V, ID=3A, VGS=10V	--	9	--	nC
Q <sub>gs</sub>	Gate Source Charge		--	1	--	nC
Q <sub>gd</sub>	Gate Drain Charge		--	2.5	--	nC
t <sub>d(on)</sub>	Turn-on Delay Time	VDD=30V, ID=3A, VGS=10V, RG=2.3Ω	--	4	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	10	--	nS
t <sub>d(off)</sub>	Turn-Off Delay Time		--	12.5	--	nS
t <sub>f</sub>	Turn-Off Fall Time		--	1.8	--	nS
<b>Source- Drain Diode Characteristics</b>						
V <sub>SD</sub>	Forward on voltage	T <sub>J</sub> =25°C, I <sub>s</sub> =3A,	--	0.8	1.2	V

## Typical Operating Characteristics



**SOT-23 Package information**


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

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